

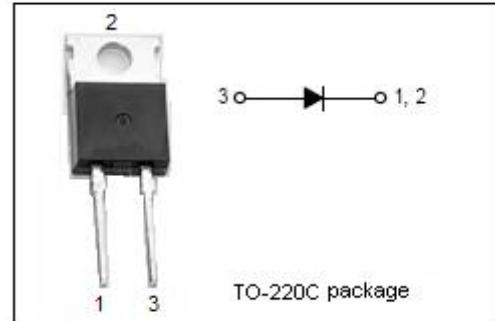


## Schottky Barrier Rectifier

ST30100

## FEATURES

- Center tap configuration
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Ultralow forward voltage drop
- High frequency operation
- Low Stored Charge Majority Carrier Conduction
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

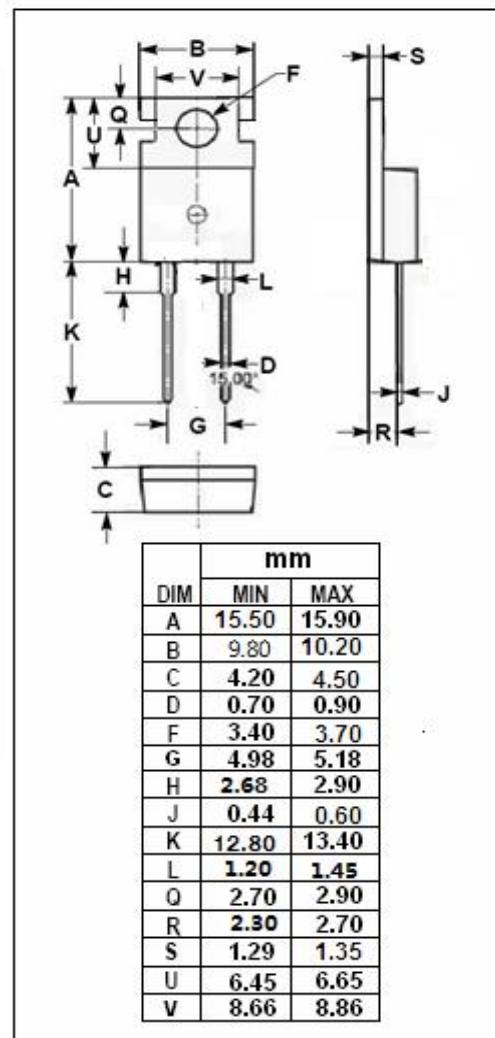


## APPLICATIONS

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{RRM}$	Peak Repetitive Reverse Voltage		
$V_{RMS}$	RMS Voltage	100	V
$V_R$	DC Blocking Voltage		
$I_{F(AV)}$	Average Rectified Forward Current (Rated $V_R$ ) $T_C = 106^\circ\text{C}$	30	A
$I_{FSM}$	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions $T_C = 150^\circ\text{C}$	300	A
$T_J$	Junction Temperature	-55~150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



INCHANGE Semiconductor

**Schottky Barrier Rectifier****ST30100****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	2.0	°C/W

**ELECTRICAL CHARACTERISTICS** (Pulse Test: Pulse Width=300 μ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V <sub>F</sub>	Maximum Instantaneous Forward Voltage	I <sub>F</sub> = 30A ; T <sub>c</sub> = 25 °C I <sub>F</sub> = 30A ; T <sub>c</sub> = 125 °C	0.75 0.70	V
I <sub>R</sub>	Maximum Instantaneous Reverse Current (Measured at 1MHz and Applied Reverse Voltage of 4.0V D.C)	V <sub>R</sub> = rated V <sub>RRM</sub> ; T <sub>c</sub> = 25 °C V <sub>R</sub> = rated V <sub>RRM</sub> ; T <sub>c</sub> = 125 °C	1 75	mA